

## 150V N-Channel MOSFET

|                |              |              |               |
|----------------|--------------|--------------|---------------|
| <b>Voltage</b> | <b>150 V</b> | <b>Rdson</b> | <b>7.5 mΩ</b> |
| <b>Current</b> | <b>125 A</b> | <b>Qg</b>    | <b>97 nC</b>  |

### Feature:

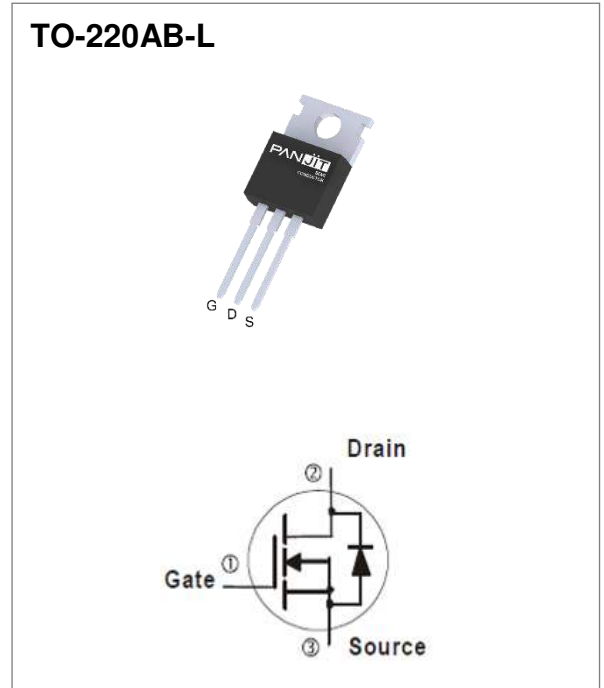
- $R_{DS(ON) Max, V_{GS}@10V}$ : 7.5mΩ
- $R_{DS(ON) Max, V_{GS}@7V}$ : 9mΩ
- High Speed Switching and Low  $R_{DS(ON)}$
- 100% Avalanche Tested
- 100% Rg Tested
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### Mechanical Data

- Case: TO-220AB-L package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0739 ounces, 2.0948 grams

### Application

- BMS, BLDC, SMPS SR.



## Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise specified)

| PARAMETER  |                         | SYMBOL         | LIMIT   | UNITS |
|--|-------------------------|----------------|---------|-------|
| Drain-Source Voltage                               |                         | $V_{DS}$       | 150     | V     |
| Gate-Source Voltage                                |                         | $V_{GS}$       | ±20     |       |
| Continuous Drain Current <sup>(Note 3)</sup>       | $T_C=25^\circ\text{C}$  | $I_D$          | 125     | A     |
|  | $T_C=100^\circ\text{C}$ |                | 88.5    |       |
| Pulsed Drain Current                               |                         | $I_{DM}$       | 350     | A     |
| Single Pulse Avalanche Current <sup>(Note 5)</sup> |                         | $I_{AS}$       | 36      | A     |
| Single Pulse Avalanche Energy <sup>(Note 5)</sup>  |                         | $E_{AS}$       | 655     | mJ    |
| Power Dissipation                                  | $T_C=25^\circ\text{C}$  | $P_D$          | 258.6   | W     |
|  | $T_C=100^\circ\text{C}$ |                | 129     |       |
| Operating Junction and Storage Temperature Range   |                         | $T_J, T_{STG}$ | -55~175 | °C    |

## Thermal Characteristics

| PARAMETER          |   | SYMBOL          | MAXIMUM | UNITS |
|--------------------|---|-----------------|---------|-------|
| Thermal Resistance | Junction-to-Case                        | $R_{\theta JC}$ | 0.58    | °C/W  |
|                    | Junction-to-Ambient <sup>(Note 3)</sup> | $R_{\theta JA}$ | 62.5    | °C/W  |

## Electrical Characteristics (T<sub>A</sub> = 25 °C unless otherwise specified)

| PARAMETER                                    | SYMBOL              | TEST CONDITION   | MIN.   | TYP. | MAX. | UNITS |
|--|---------------------|--|--|------|------|-------|
| <b>Static</b>                                |                     |  |  |      |      |       |
| Drain-Source Breakdown Voltage               | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V, I <sub>D</sub> =250uA                         | 150  | -    | -    | V     |
| Gate Threshold Voltage                       | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA           | 2  | 3.2  | 4    |       |
| Drain-Source On-State Resistance<br>(Note 1) | R <sub>DS(on)</sub> | V <sub>GS</sub> =10V, I <sub>D</sub> =50A                          | -  | 6.3  | 7.5  | mΩ    |
|  | R <sub>DS(on)</sub> | V <sub>GS</sub> =7V, I <sub>D</sub> =25A                           | -  | 6.8  | 9    |       |
| Zero Gate Voltage Drain Current              | I <sub>DSS</sub>    | V <sub>DS</sub> =120V, V <sub>GS</sub> =0V                         | -  | -    | 1    | uA    |
| Gate-Source Leakage Current                  | I <sub>GSS</sub>    | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V                         | -  | -    | ±100 | nA    |
| <b>Dynamic</b> (Note 6)                      |                     |  |  |      |      |       |
| Total Gate Charge                            | Q <sub>g</sub>      | V <sub>DS</sub> =75V, I <sub>D</sub> =50A,<br>V <sub>GS</sub> =7V  | -  | 72   | -    | nC    |
|  | Q <sub>g</sub>      | V <sub>DS</sub> =75V, I <sub>D</sub> =50A,<br>V <sub>GS</sub> =10V | -  | 97   | -    |       |
| Gate-Source Charge                           | Q <sub>gs</sub>     | V <sub>DS</sub> =75V, I <sub>D</sub> =50A,<br>V <sub>GS</sub> =10V | -  | 31   | -    |       |
| Gate-Drain Charge                            | Q <sub>gd</sub>     | V <sub>DS</sub> =75V, I <sub>D</sub> =50A,<br>V <sub>GS</sub> =10V | -  | 23   | -    |       |
| Input Capacitance                            | C <sub>iss</sub>    | V <sub>DS</sub> =75V, V <sub>GS</sub> =0V,<br>F=1MHz               | -  | 6511 | -    | pF    |
| Output Capacitance                           | C <sub>oss</sub>    |  | -  | 862  | -    |       |
| Reverse Transfer Capacitance                 | C <sub>rss</sub>    |  | -  | 83   | -    |       |
| Turn-On Delay Time                           | t <sub>d(on)</sub>  |  | V <sub>DD</sub> =75V, I <sub>D</sub> =50A,<br>V <sub>GS</sub> =10V, R <sub>G</sub> =2Ω<br>(Note 2) | -    | 53   |       |
| Turn-On Rise Time                            | t <sub>r</sub>      | -  |  | 111  | -    |       |
| Turn-Off Delay Time                          | t <sub>d(off)</sub> | -  |  | 99   | -    |       |
| Turn-Off Fall Time                           | t <sub>f</sub>      | -  |  | 113  | -    |       |
| Gate Resistance                              | R <sub>g</sub>      | f=1.0MHz   |  | -    | 2.7  | -     |
| <b>Drain-Source Diode</b>                    |                     |  |  |      |      |       |
| Diode Forward Voltage                        | V <sub>SD</sub>     | I <sub>S</sub> =50A, V <sub>GS</sub> =0V                           | -  | 0.9  | 1.3  | V     |
| Reverse Recovery Charge                      | Q <sub>rr</sub>     | I <sub>S</sub> =50A  | -  | 541  | -    | nC    |
| Reverse Recovery Time                        | T <sub>rr</sub>     | di/dt=100A/μs  | -  | 117  | -    | ns    |

NOTES :

- Pulse width<300us, Duty cycle<2%
- Essentially independent of operating temperature typical characteristics.
- The maximum current rating is silicon limited.
- RθJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- The test condition is L=1mH, IAS=36.2A, VDD=50V, VGS=10V, RG=25ohm, Starting T<sub>J</sub>=25 °C
- Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTIC CURVES

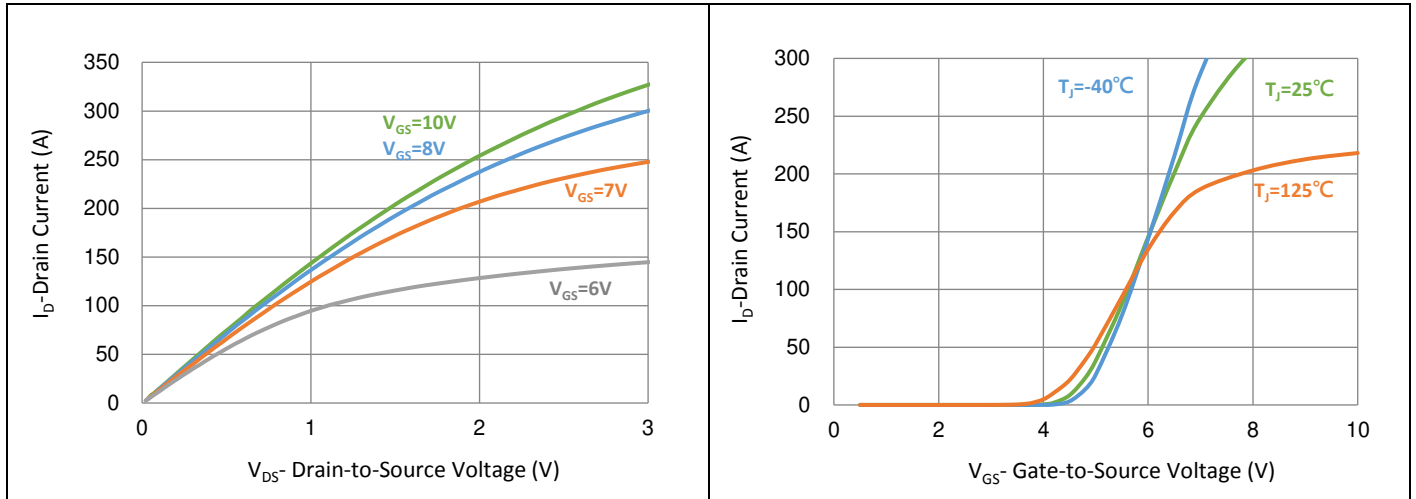


Fig.1 Output Characteristics

Fig.2 Transfer Characteristics

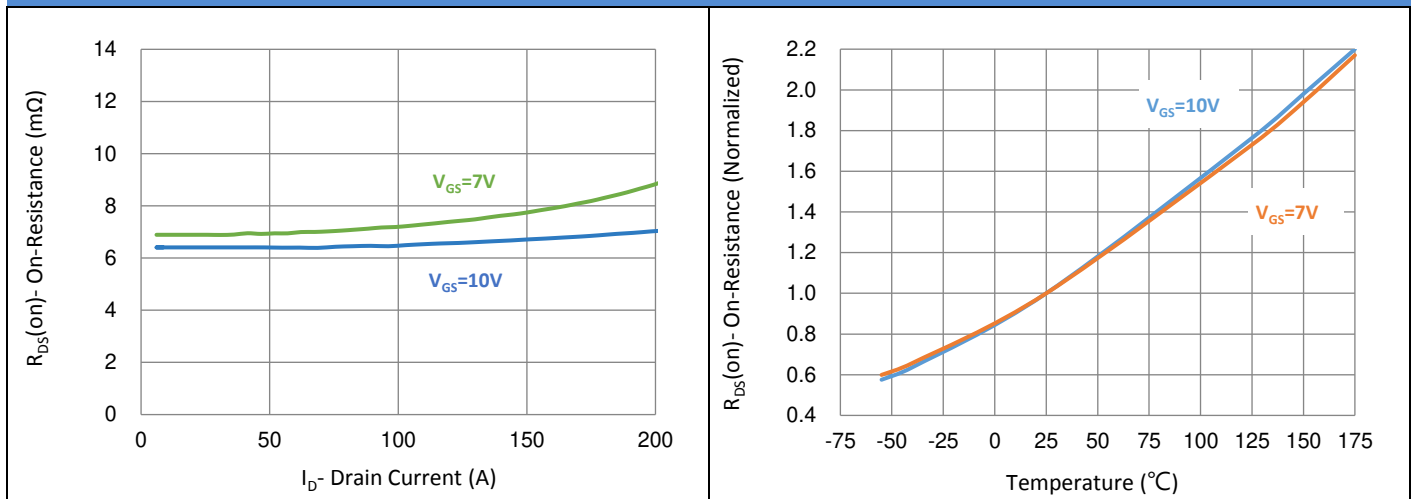


Fig.3 On-Resistance vs. Drain Current

Fig.4 On-Resistance vs. Junction Temperature

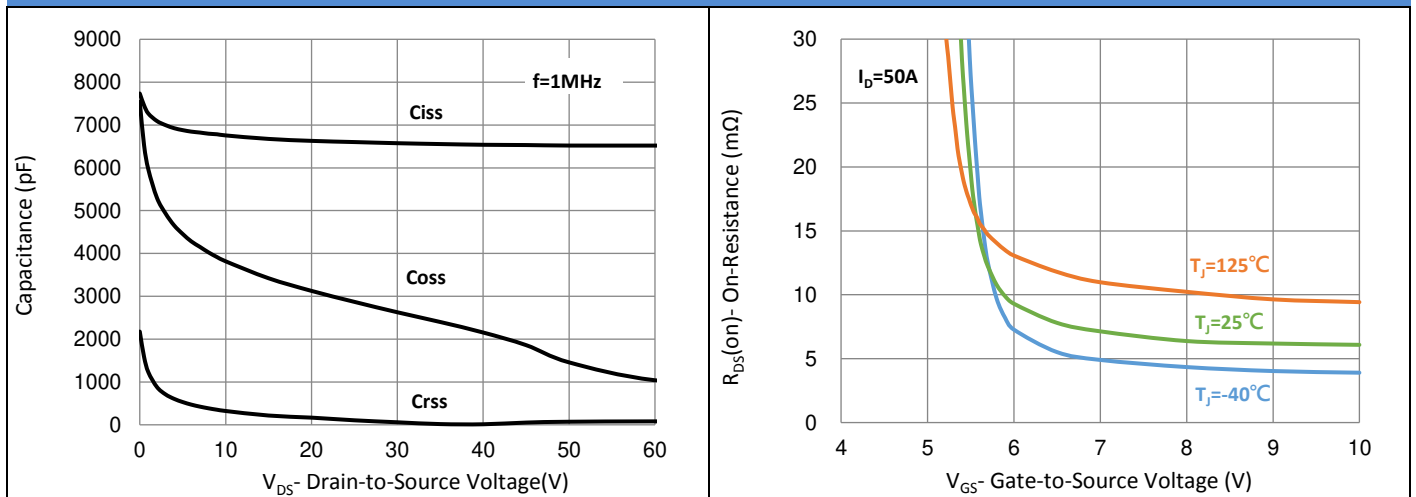


Fig.5 Capacitance vs. Drain-Source Voltage

Fig.6 On-Resistance vs. Gate-Source Voltage

TYPICAL CHARACTERISTIC CURVES

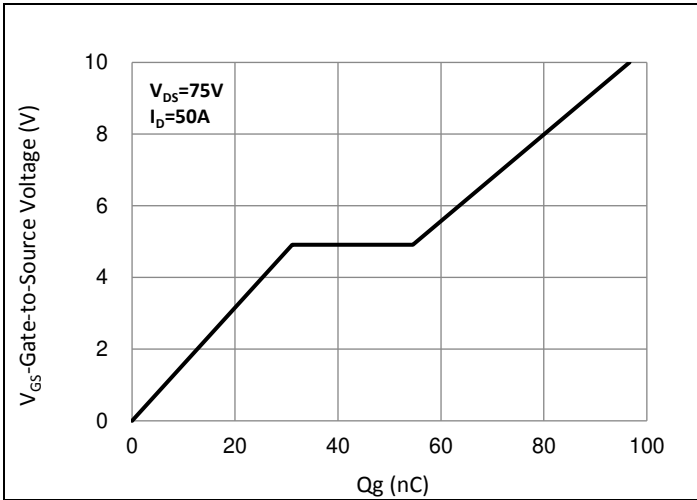


Fig.7 Gate-Charge Characteristics

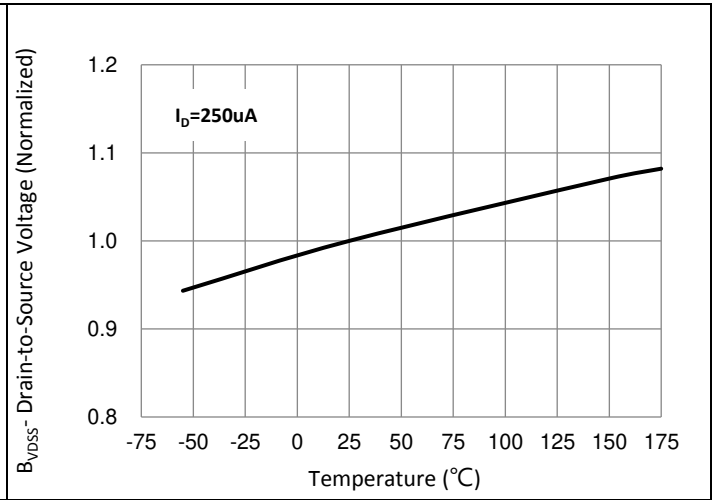


Fig.8 Breakdown Voltage Variation vs. Temperature

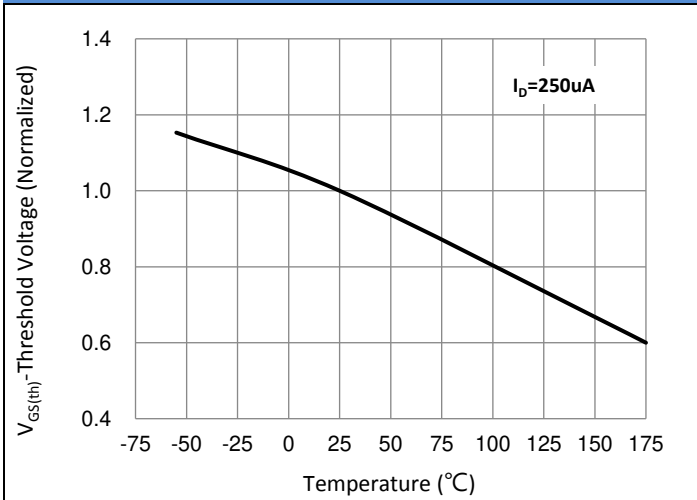


Fig.9 Threshold Voltage Variation with Temperature

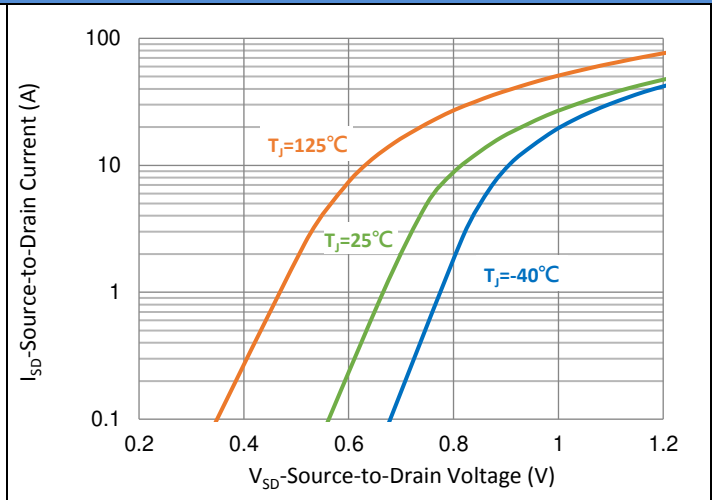


Fig.10 Source-Drain Diode Forward Voltage

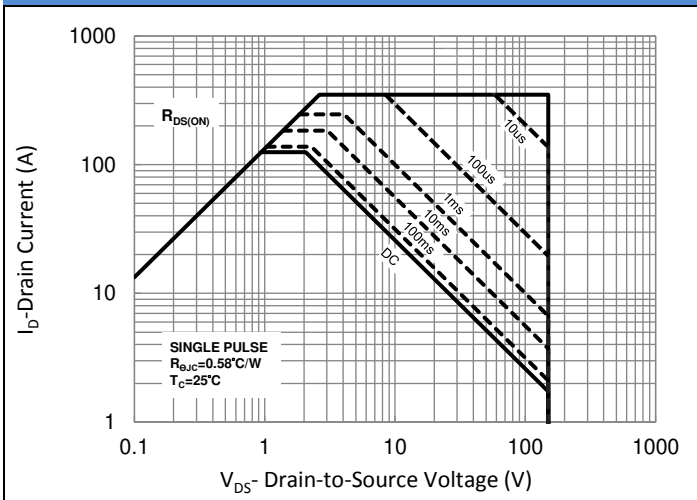


Fig.11 Maximum Safe Operating Area

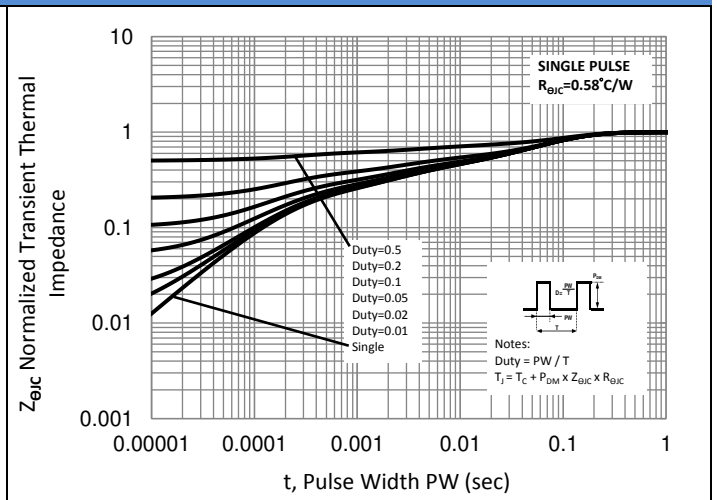


Fig.12 Normalized Transient Thermal Impedance

## TYPICAL CHARACTERISTIC CURVES

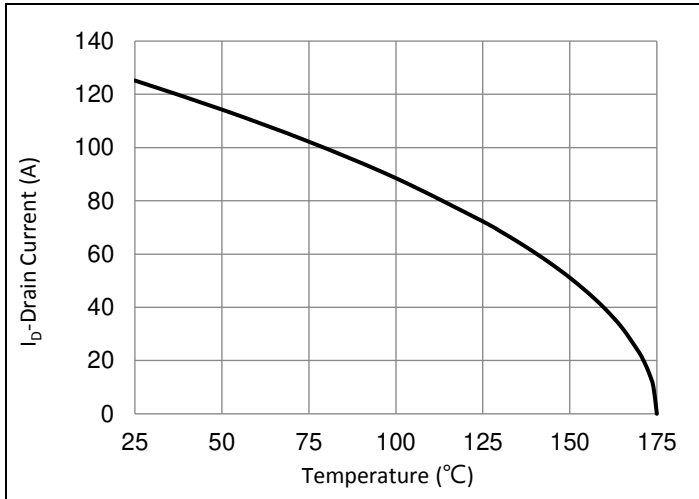
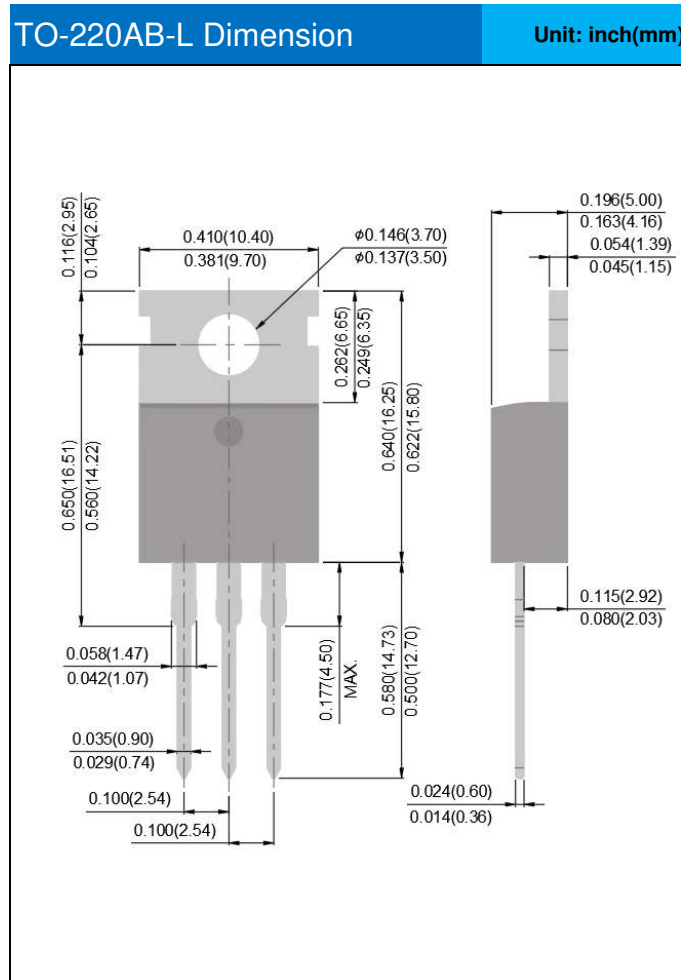


Fig.13 Drain Current vs. Case Temperature

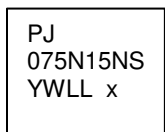
**Product and Packing Information**

| Part No.      | Package Type | Packing Type | Marking  |
|---------------|--------------|--------------|----------|
| PSMP075N15NS1 | TO-220AB-L   | 50pcs / Tube | 075N15NS |

**Packaging Information**



**Marking Diagram**



- Y** = Year Code
- W** = Week Code (A~Z)
- LL** = Lot Code (00~99)
- x** = Production Line Code

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